

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

SPI11N60C3

D(2)

5(3)

pin 1, Gate 2, Drain

mm

MIN MAX 4.37 4.77

1.42

2.87

0.97

1.42

0.53

8.90

10.39

- 1.31 13.34 14.10

4.06

1.15

1.25 1.50

23.20 24.02

4.37

2.47 0.70

1.17

8.38

6.00

9.90

7.30 -2.54BSC

3.30

0.95

DIM

A

A1

A2

Ъ

Ъ2

с

D

D1

D2

Ε

E4

eG

H2

L

L1

L3

3, Source

TO-262 package

3

2

• FEATURES

- Static drain-source on-resistance: R⊳s(on) ≤0.38Ω
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

- Ultra low gate charge
- High peak current capability
- Improved transconductance

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	600	V	
V _{GS}	Gate-Source Voltage	±20	V	
ID	Drain Current-Continuous	А		
I _{DM}	Drain Current-Single Pulsed 33		А	
PD	Total Dissipation @Tc=25°C 125		W	
Tj	Max. Operating Junction Temperature	ax. Operating Junction Temperature 150		
T _{stg}	Storage Temperature	-55~150	°C	

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	1	°C/W	



1



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =0.25mA	600			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =0.5mA	2.1		3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; ID=7A			0.38	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} =30V; V _{DS} =0V			0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			1	μA
V _{SD}	Diode forward voltage	I _F =IS; V _{GS} = 0V			1.2	V

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